

A2 5. (Amended) A method as claimed in claim 1, characterized in that the vertical portion of the smaller isolation layer (402) is isotropically etched.

8. (Amended) An integrated circuit as claimed in claim 6, characterized in that the depth (h) of the trench (TR) is equal to maximally half the height (H1) of the larger isolation layer and equal to maximally half the thickness (E) of the larger isolation layer.

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Sub 3
"Sub 3"
9. (Amended) An integrated circuit as claimed in claim 6, characterized in that each lateral isolation region comprises a horizontal trench (TH) made in the smaller isolation layer (402) between the larger isolation layer (411) and the substrate (1) of the integrated circuit, said trench extending from the lateral edge of the larger isolation layer of the lateral isolation region.

REMARKS

The claims have been amended in order to reformat the claims to delete all multiple dependencies prior to calculation of the filing fee and place the instant application in standard U.S. format.